

RoHS Compliant Product  
 A suffix of "-C" specifies halogen and lead-free

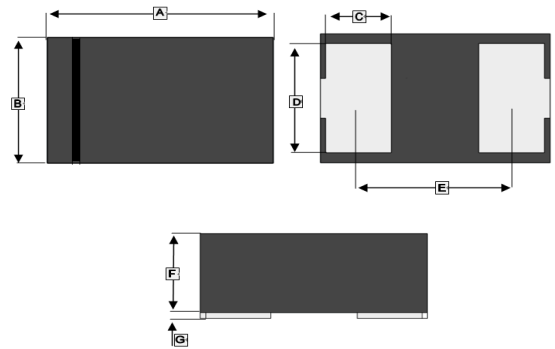
**DESCRIPTION**

SBESD0801S is a low-capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With typical capacitance of 0.35pF only, SBESD0801S is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 ( $\pm 15\text{kV}$  air,  $\pm 8\text{kV}$  contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A,5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

SBESD0801S uses ultra-small DFN1006-2L package. Each SBESD0801S device can protect one high-speed data line. It offers system designers flexibility to protect single data line where space is a premium concern. The combined features of low capacitance, ultra-small size and high ESD robustness make

SBESD0801S ideal for high-speed data port and high-frequency line (e.g., USB 2.0 & antenna line) applications, such as cellular phones and HD visual devices.

**DFN1006-2L**



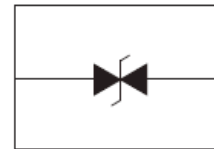
REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.95	1.05	E	0.65 TYP.	
B	0.55	0.65	F	0.3	0.4
C	0.2	0.3	G	0.00	0.05
D	0.45	0.55			

**MACHANICAL DATA**

- Flammability Rating: UL 94V-0
- High temperature soldering guaranteed: 260°C / 10s

**APPLICATIONS**

- Mobile phone
- PAD
- Notebook
- LCD TV
- MDDI Ports
- Digital Visual Interfaces (DVI)



**Bi-direction**

**FEATURES**

- Ultra-low clamping voltage
- Low leakage current
- Small package

**MARKING**



**PACKAGE INFORMATION**

Package	MPQ	Leader Size
DFN1006-2L	10K	7 inch

**ABSOLUTE MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

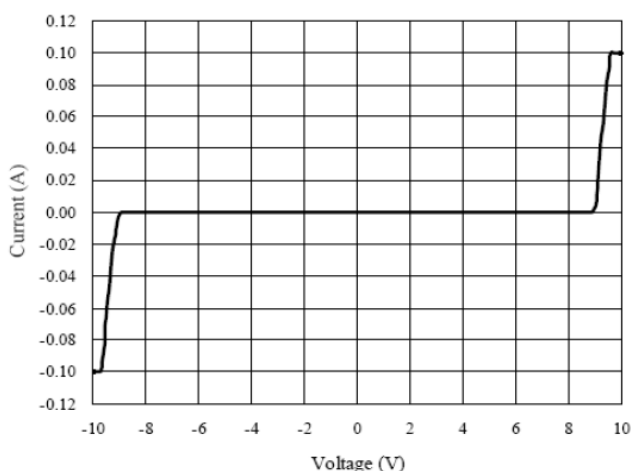
Rating		Symbol	Value	Unit
IEC 61000-4-2 (ESD)	Air contact		$\pm 17$	kV
	Contact discharge		$\pm 12$	
Peak pulse power ( $t_p=8/20\mu\text{s}$ )		$P_{PK}$	56	W
Peak pulse current ( $t_p=8/20\mu\text{s}$ )		$I_{PP}$	2	A
Storage temperature range		$T_J, T_{STG}$	-55~125 , -55 ~ 150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

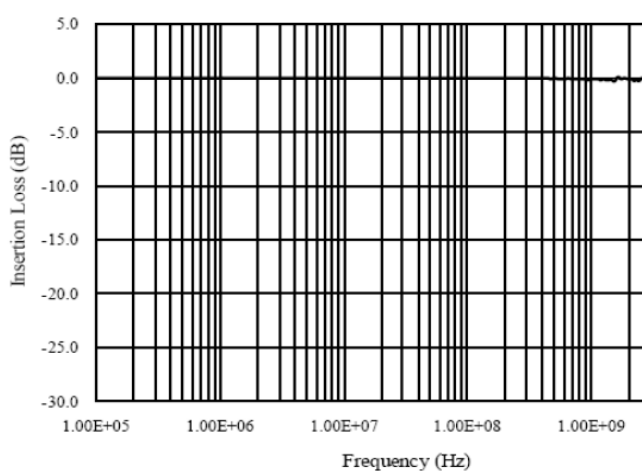
Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Reveres maximum working voltage	$V_{RWM}$		-	-	5	V
Reveres leakage current	$I_R$	$V_{RWM}=5\text{V}$	-	0.01	1	$\mu\text{A}$
Reveres breakdown voltage	$V_{BR}$	$I_T=1\text{mA}$	6	8.8	11	V
Clamping Voltage	$V_C$	$I_{PP}=1\text{A}, t_p=8/20\mu\text{s}$	-	-	12	V
		$I_{PP}=2\text{A}, t_p=8/20\mu\text{s}$	-	-	14	V
Junction capacitance	$C_J$	$f=1\text{MHz}, V_R=0$	-	0.35	0.5	pF

**RATINGS AND CHARACTERISTICS CURVES**

**Voltage Sweeping of I/O to I/O**

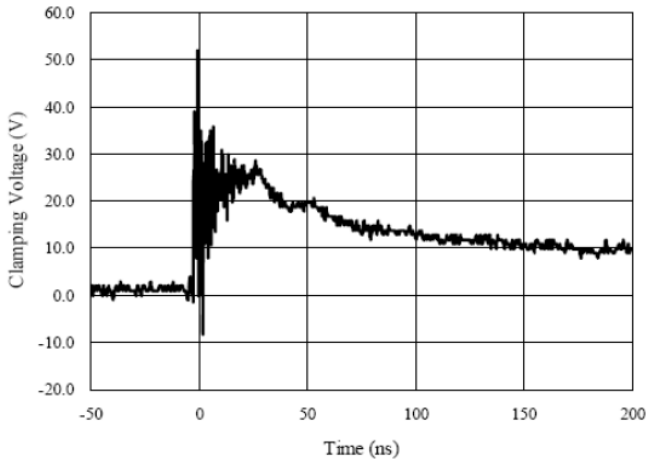


**Insertion Loss S21 of I/O to I/O**

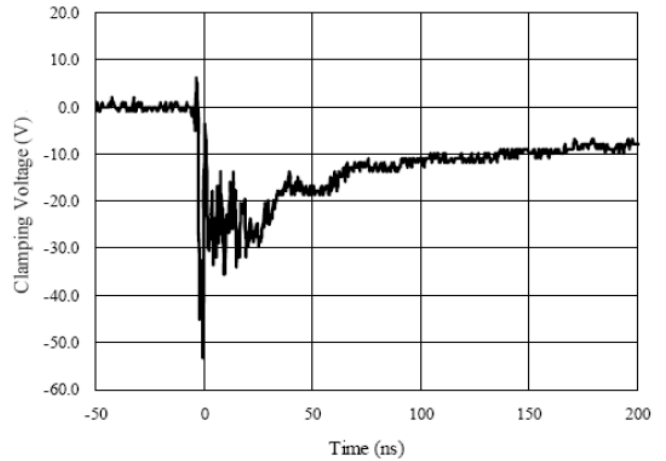


**RATINGS AND CHARACTERISTICS CURVES**

**ESD Clamping of I/O to I/O  
(+8kV Contact per IEC 61000-4-2)**

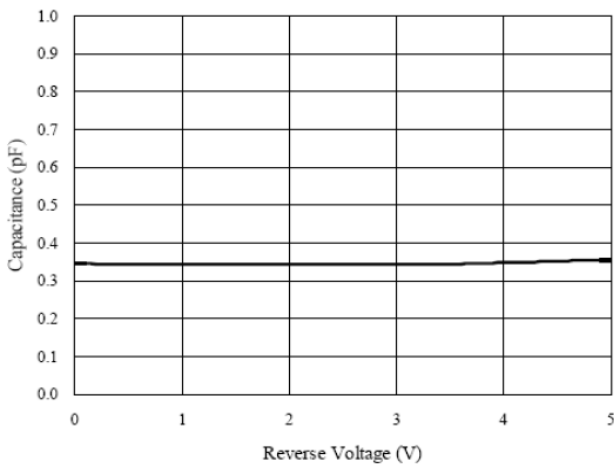


**ESD Clamping of I/O to I/O  
(-8kV Contact per IEC 61000-4-2)**



**Capacitance vs. Voltage of I/O to I/O (f = 1MHz)**

Capacitance vs. Reverse Voltage



Normalized Capacitance vs. Reverse Voltage

